Features

- AEC-Q101 Qualified
- Trench Power MV MOSFET Technology
- Low Thermal Resistance
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-CHANNEL MOSFET

Maximum Ratings

- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 60°C/W Junction to Ambient (Note2)
- Thermal Resistance: 6°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	-8	A
	T_C=100°C		-5	
Pulsed Drain Current(Note3)		I_{DM}	-32	A
Total Power Dissipation(Note4)		P_D	20.8	W
Single Pulsed Avalanche Energy(Note5)		E_{AS}	50	mJ

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{DD}= -50V, V_{GS}=-10V,R_G=25Ω,L=1 mH.

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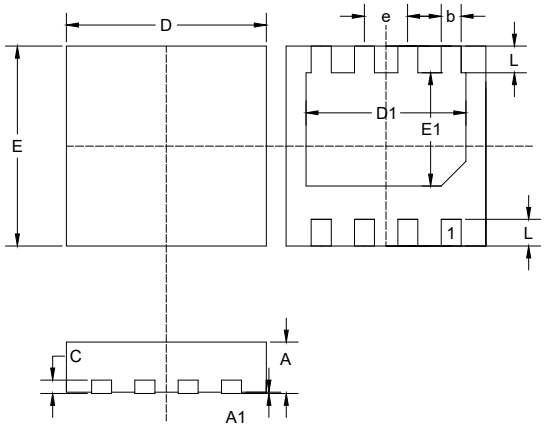
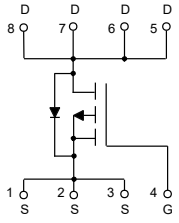
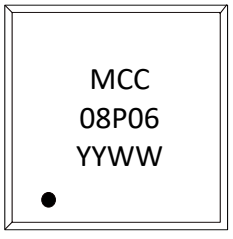


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.028	0.031	0.70	0.80	
A1	0.000	0.002	0.00	0.05	
C	0.008		0.20		TYP.
b	0.010	0.014	0.25	0.35	
D	0.130		3.30		TYP.
E	0.130		3.30		TYP.
e	0.026		0.65		TYP.
D1	0.100	0.110	2.55	2.80	
E1	0.065	0.074	1.64	1.89	
L	0.013	0.021	0.325	0.525	

Internal Structure and Marking Code





pin1

YYWW: 4 codes in total
YY is the year
WW is the week

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-48V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.9	-3	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-6A		20	28.4	mΩ
		V_{GS}=-4.5V, I_D=-3A		24	39.3	
Gate Resistance	R_g	f=1Mhz， Open drain		5		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-8	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-3A			-1.3	V
Reverse Recovery Time	t_{rr}	I_F=-15A, dI_F/dt=100A/μs		29		ns
Reverse Recovery Charge	Q_{rr}			38		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-30V,V_{GS}=0V,f=1MHz		4306		pF
Output Capacitance	C_{oss}			178		
Reverse Transfer Capacitance	C_{rss}			158		
Total Gate Charge	Q_g	V_{DS}=-30V,V_{GS}=-10V,I_D=-15A		61		nC
Gate-Source Charge	Q_{gs}			17		
Gate-Drain Charge	Q_{gd}			7.1		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-30V, V_{GS}=-10V, R_{GEN}=4.5Ω, I_{DS}=-15A		62		ns
Turn-On Rise Time	t_r			79		
Turn-Off Delay Time	$t_{d(off)}$			376		
Turn-Off Fall Time	t_f			161		

Curve Characteristics

Fig.1 - Typical Output Characteristics

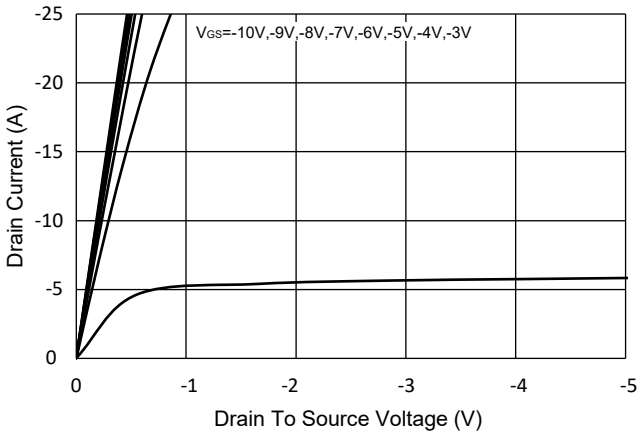


Fig.2 - Transfer Characteristic

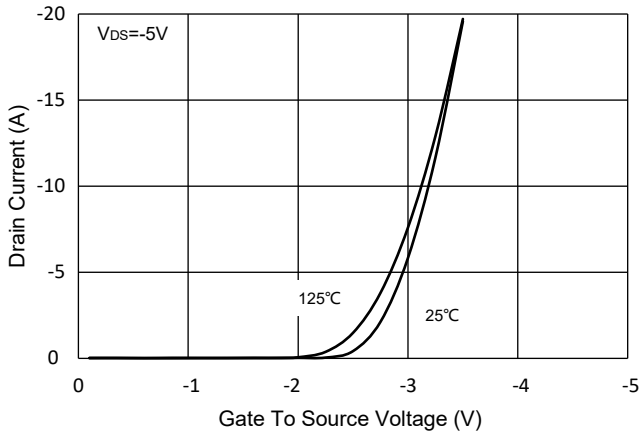


Fig.3 - $R_{DS(ON)}$ - V_{GS}

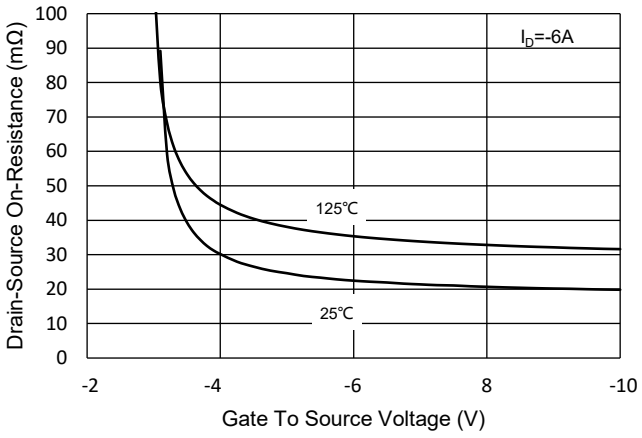


Fig. 4 - $R_{DS(ON)}$—I_D

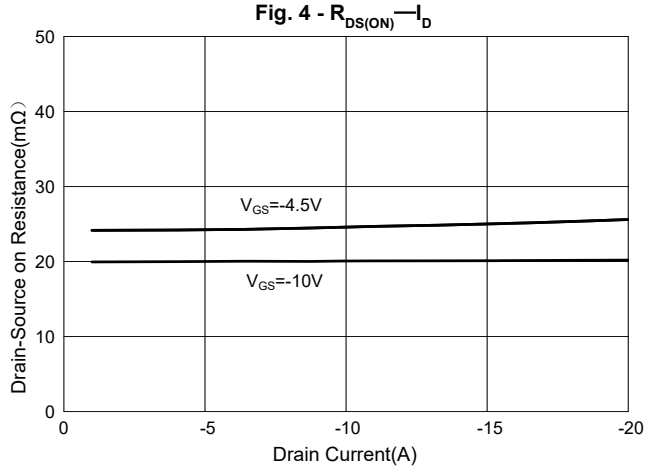


Fig.5 - Capacitance Characteristics

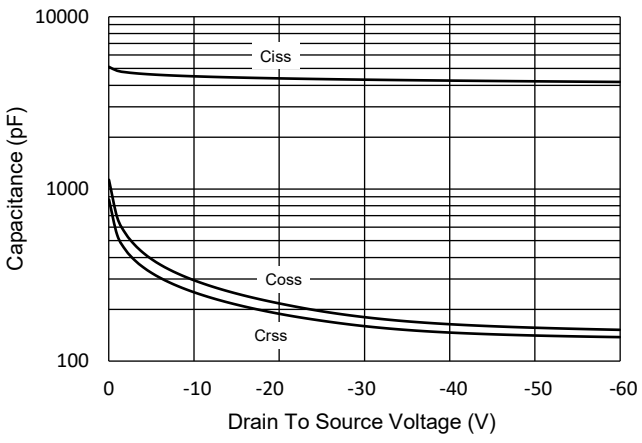
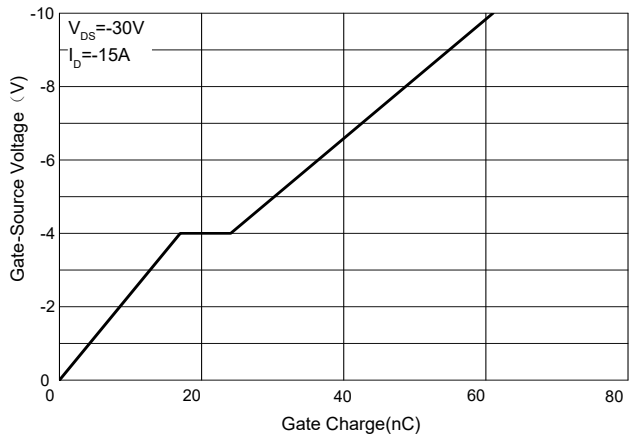


Fig. 6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

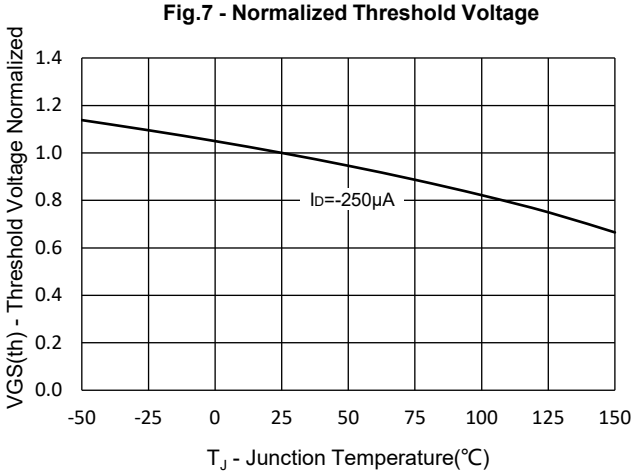


Fig.8 - Normalized On Resistance Characteristics

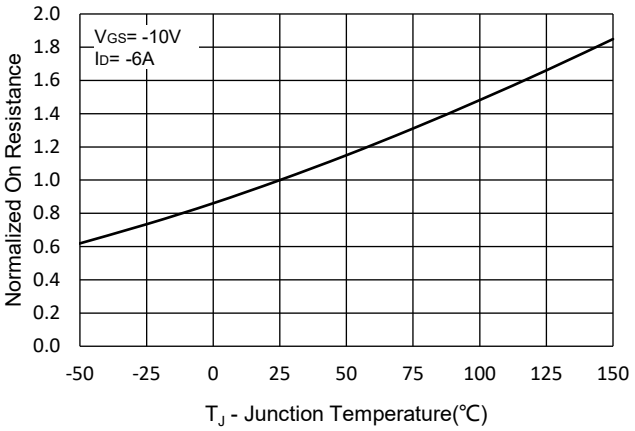


Fig.9 - I_S - V_{SD}

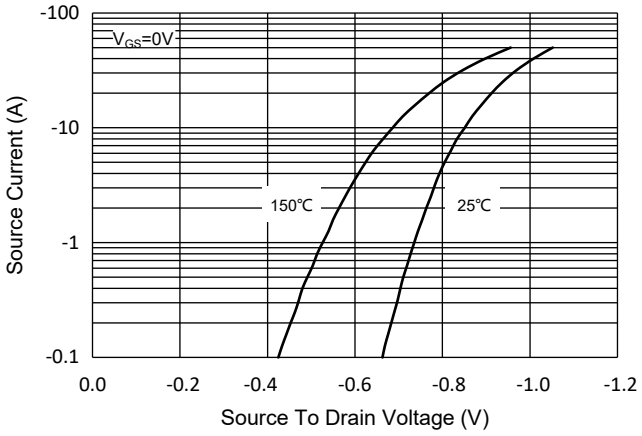


Fig.10 - Drain Current

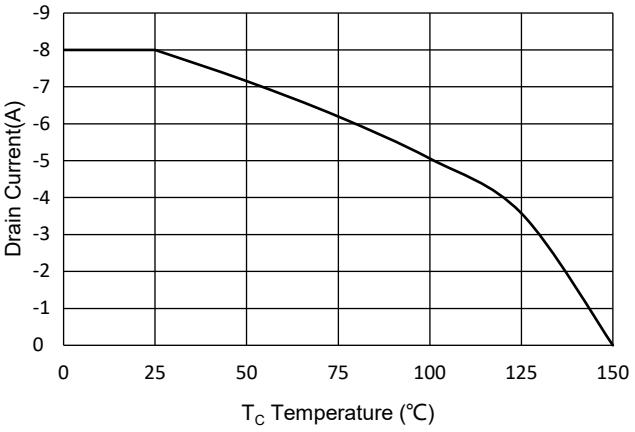
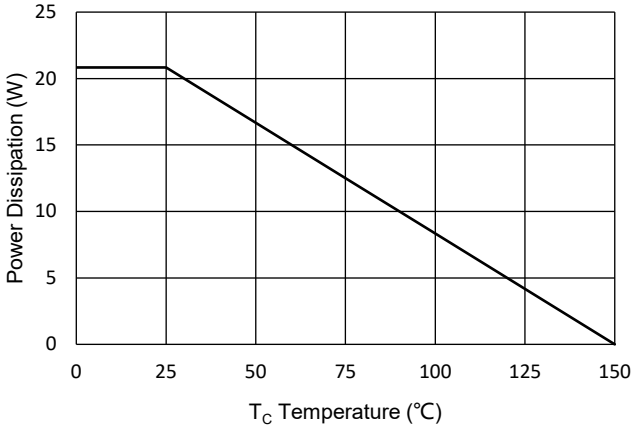


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

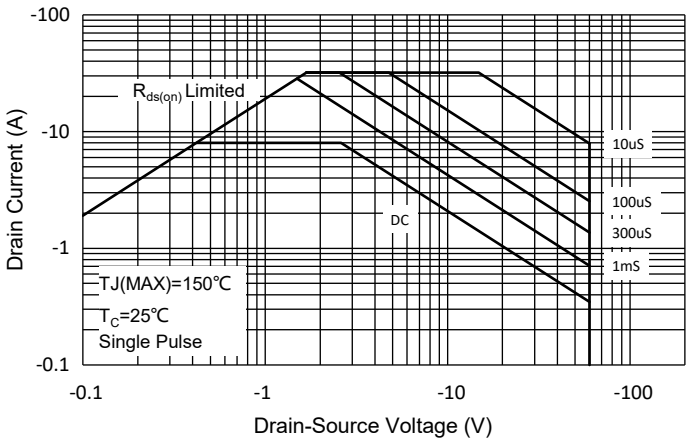
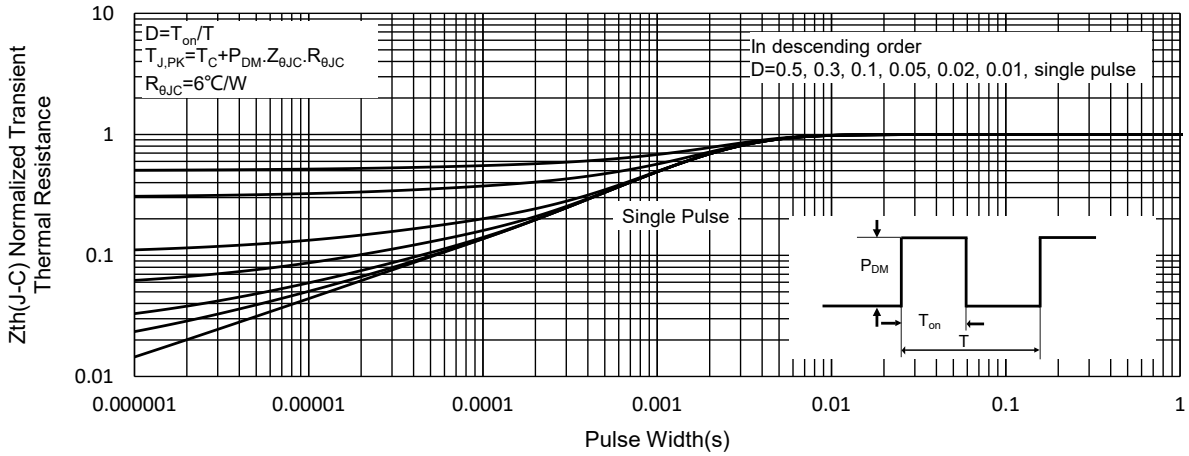


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel